General Description

The NPD40N06 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The NPD40N06 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

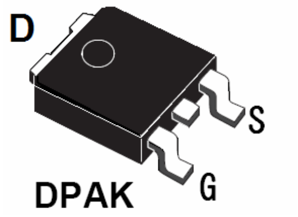
Features

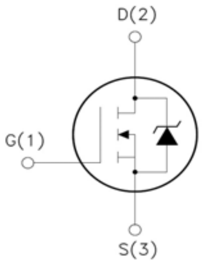
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

BVDSS	RDSON	ID
60V	20mΩ	40A

RoHS COMPLIANT





1.Gate (G)
2.Drain (D)
3.Source (S)

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	40	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	32	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	10	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	8	A
I_{DM}	Pulsed Drain Current[2]	200	A
EAS	Single Pulse Avalanche Energy[3]	42	mJ
I_{AS}	Avalanche Current	28	A
P_D@T_C=25℃	Total Power Dissipation[4]	53	W
P_D@T_A=25℃	Total Power Dissipation[4]	3.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	2	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
△BV_{DSS}/△T_J	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.057	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	20	23	mΩ
		V_{GS}=4.5V , I_D=10A	---	23	28	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.8	2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.68	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=15A	---	33	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	3.4	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=30V , V_{GS}=4.5V , I_D=15A	---	28	36	nC
Q_{gs}	Gate-Source Charge		---	3.5	10	
Q_{gd}	Gate-Drain Charge		---	6.5	15	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3Ω, I_D=15A	---	7.2	14.4	ns
T_r	Rise Time		---	38	90	
$T_{d(off)}$	Turn-Off Delay Time		---	34	73	
T_f	Fall Time		---	8.2	15.2	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1680	2578	pF
C_{oss}	Output Capacitance		---	115	203	
C_{rss}	Reverse Transfer Capacitance		---	85	136	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=25V , L=0.1mH , I_{AS}=15A	19	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	50	A
I_{SM}	Pulsed Source Current[2,6]		---	---	200	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=20A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=1A ,dI/dt=100A/μs,TJ=25℃	---	19.6	---	nS
Q_{rr}	Reverse Recovery Charge		---	14.2	---	nC

Note :

1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper,t<10sec.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=15A

4.The power dissipation is limited by 150℃ junction temperature

5.The Min. value is 100% EAS tested guarantee.

6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

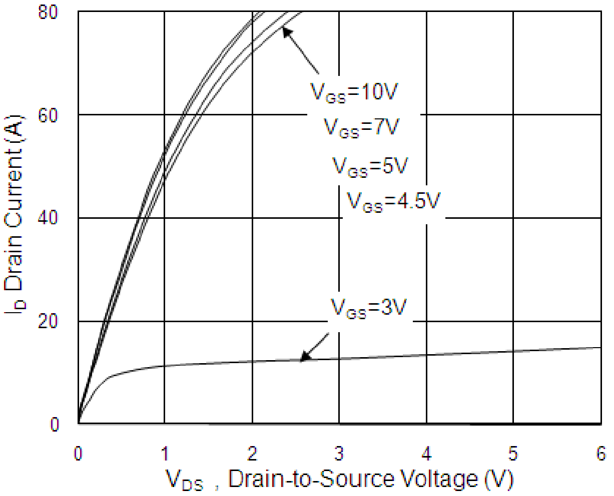


Fig.1 Typical Output Characteristics

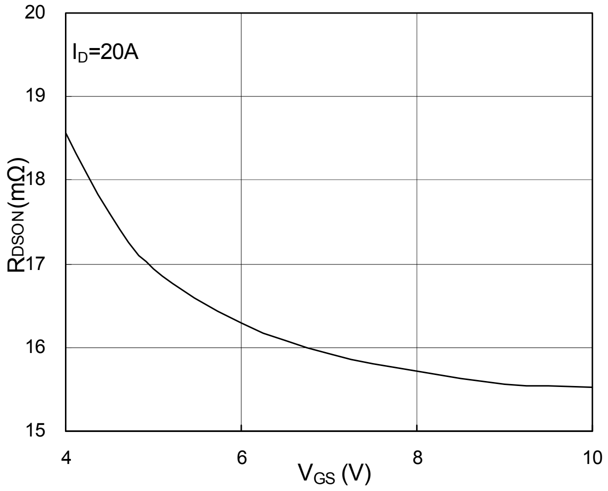


Fig.2 On-Resistance v.s Gate-Source

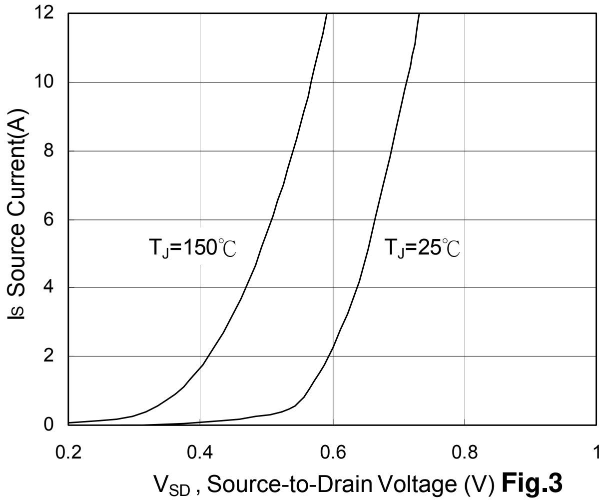


Fig.3

Forward Characteristics of Reverse

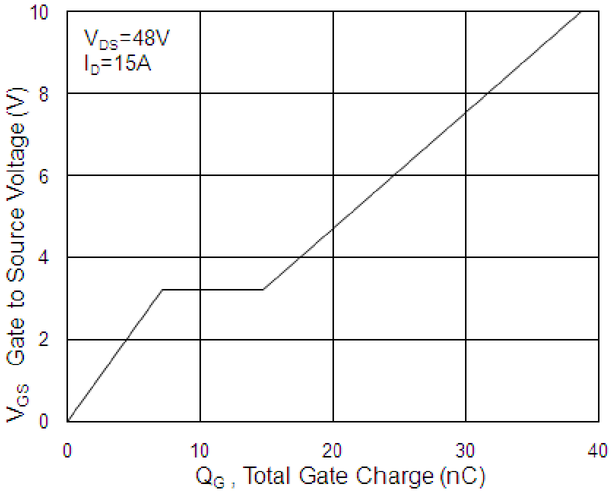


Fig.4 Gate-Charge Characteristics

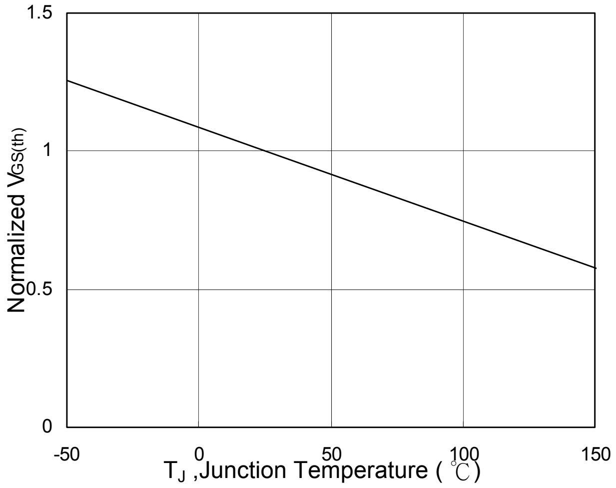


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

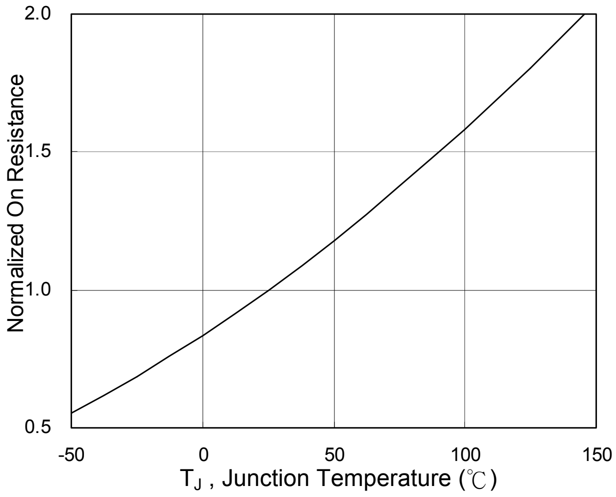


Fig.6 Normalized R_{DSON} v.s T_J

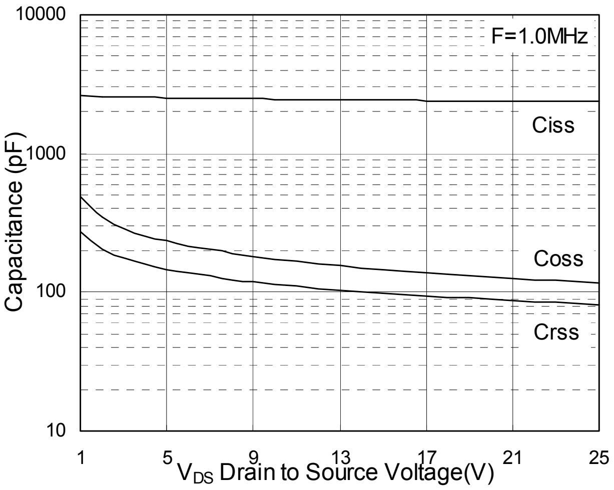


Fig.7 Capacitance

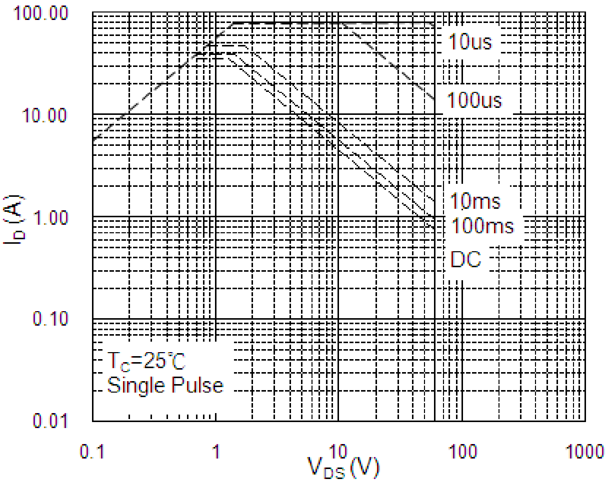


Fig.8 Safe Operating Area

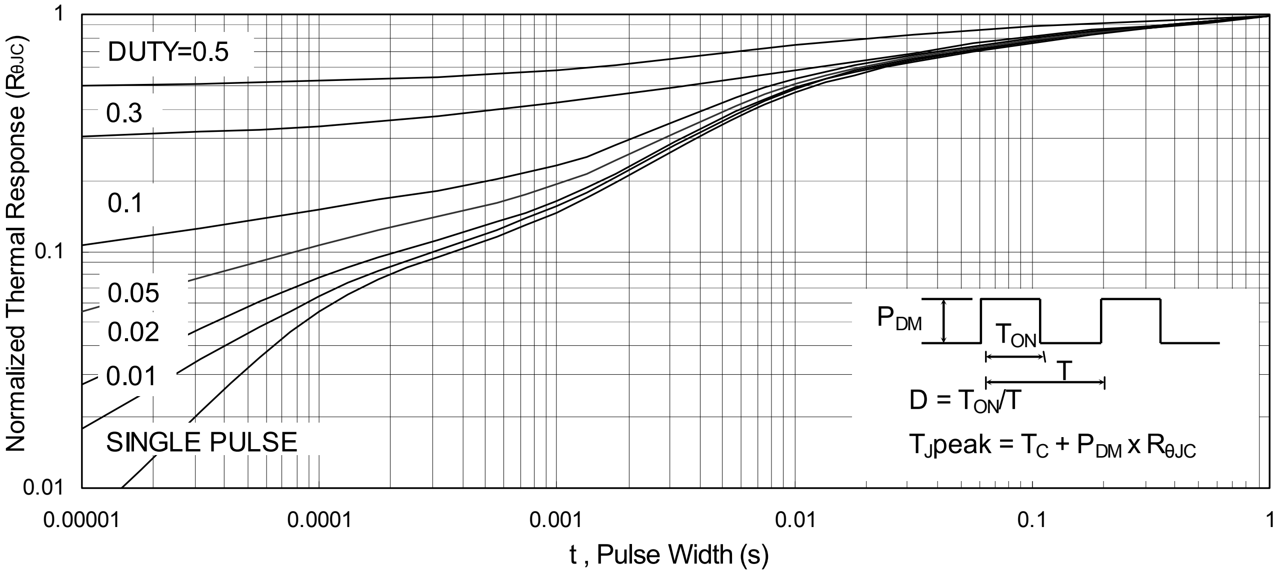


Fig.9 Normalized Maximum Transient Thermal Impedance

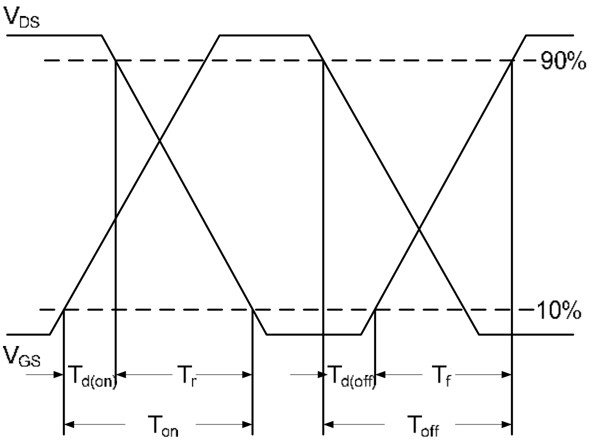


Fig.10 Switching Time Waveform

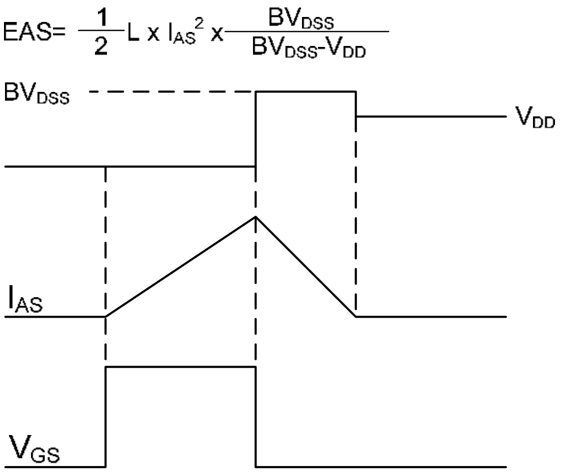


Fig.11 Unclamped Inductive Switching Waveform